	L #	Hits	S arch T xt	DB
1	L1	1014	(361/761,762,763,764).ccls.	USPAT; US-PGPUB
2	L2	1118	(361/792,793,794,795).ccls.	USPAT; US-PGPUB
3	L3	3672	(343/700MS,702,873).ccls.	USPAT; US-PGPUB
4	L4	65	(257/e27.113,e27.114).ccls.	USPAT; US-PGPUB
5	L5	5710	1 2 3 4	USPAT; US-PGPUB
6	L6	119	5 and @pd>=20030519	USPAT; US-PGPUB
7	L7	13	6 and ((silicon polysilicon (gallium adj arsenide) si gaas semiconductor (integrated adj circuit$1)) with layer$2)	USPAT; US-PGPUB

	L #	Hit	S arch Text	DB
8	L8	106	6 not 7	USPAT; US-PGPUB
9	L9	93	8 and (capacitor$1 condenser$1 antenna$1 aerial$1 coil$1)	USPAT; US-PGPUB
10	L10	13	8 not 9	USPAT; US-PGPUB
11	L11	1284	(257/728,724).ccls.	USPAT; US-PGPUB
12	L12	24	11 and @pd>=20030519	USPAT; US-PGPUB
13	L13	842	257/700.ccls.	USPAT; US-PGPUB
14	L14	801	(361/780,782,783).ccls.	USPAT; US-PGPUB

	L #	Hits	S arch T xt	DBs
15	L15	1601	13 14	USP AT; US-P GPU B
16	L16	799	15 and ((silicon polysilicon (gallium adj arsenide) si gaas semiconductor (integrated adj circuit$1)) with layer$2)	USP AT; US-P GPU B
17	L17	299	16 and (capacitor$1 condenser$1 antenna$1 aerial$1 coil$1)	USP AT; US-P GPU B
18	L18	295	17 not (6 12)	USP AT; US-P GPU B
19	L19	684	(257/759,760).ccls.	USP AT; US-P GPU B
20	L20	166	19 and (capacitor$1 condenser$1 antenna$1 aerial$1 coil$1)	USP AT; US-P GPU B
21	L21	154	20 not (6 12 18)	USP AT; US-P GPU B